Silicon PNP Power Transistors 2SA1359

DESCRIPTION

·With TO-126 package
·Complement to type 2SC3422
·Good linearity of h_{FE}

APPLICATIONS

·Audio frequency amplifier
·Low speed switching
·Suitable for output stage of 5W car radio and car stereo

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

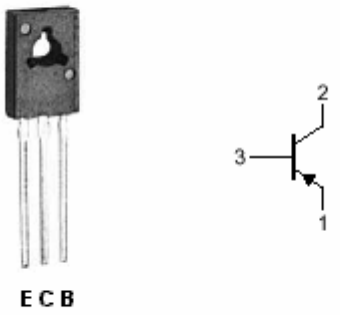

Fig.1 simplified outline (TO-126) and symbol

Absolute maximum ratings(Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-40	V
V_{CEO}	Collector-emitter voltage	Open base	-40	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-3	A
I_B	Base current		-1	A
P_D	Total power dissipation	T_a=25□	1.5	W
		T_C=25□	10	
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55□+150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=-10mA ;I_B=0	-40			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=-2A; I_B=-0.2A			-0.8	V
V_{BE}	Base-emitter on voltage	I_C=-0.5A ; V_{CE}=-2V			-1.0	V
I_{CBO}	Collector cut-off current	V_{CB}=-40V; I_E=0			-0.1	μA
I_{EBO}	Emitter cut-off current	V_{EB}=-5V; I_C=0			-0.1	μA
h_{FE-1}	DC current gain	I_C=-0.5A ; V_{CE}=-2V	80		240	
h_{FE-2}	DC current gain	I_C=-2.5A ; V_{CE}=-2V	25			
C_{ob}	Output capacitance	I_E=0 ; V_{CB}=-10V f=1MHz		35		pF
f_T	Transition frequency	I_C=-0.5A ; V_{CE}=-2V		100		MHz

◆ **h_{FE-1} Classifications**

O	Y
80-160	120-240

PACKAGE OUTLINE

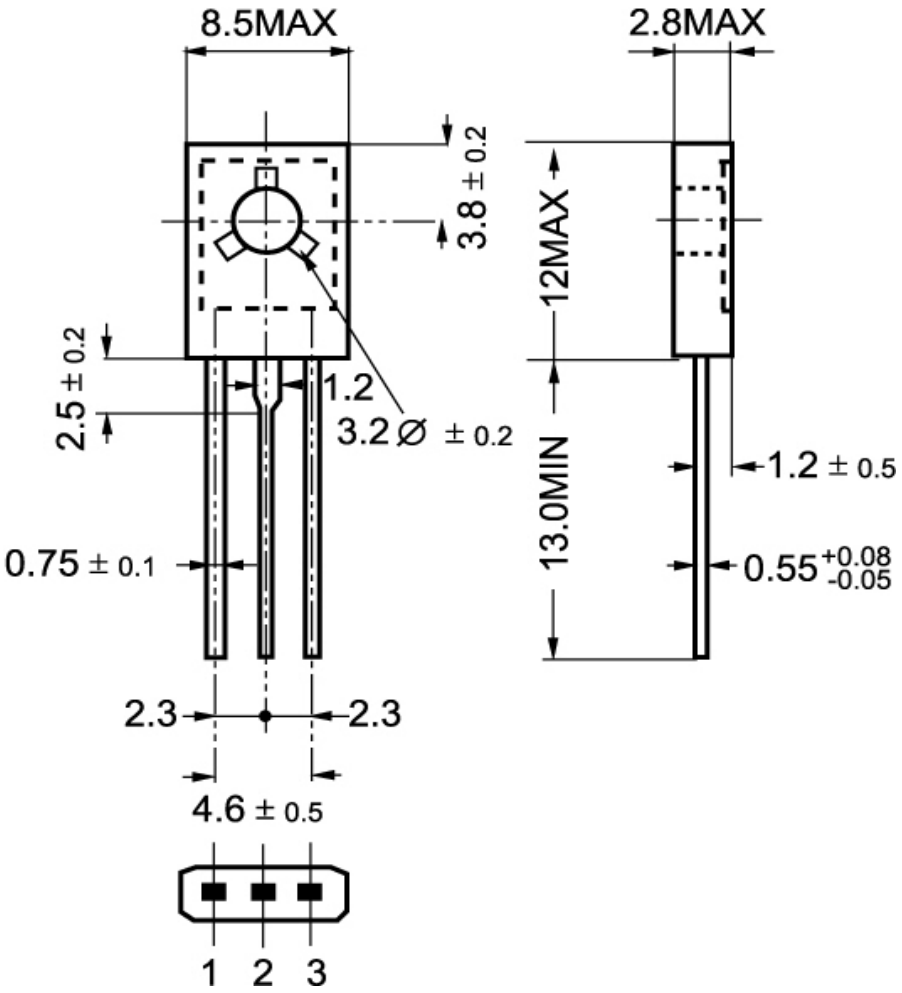

Fig.2 Outline dimensions

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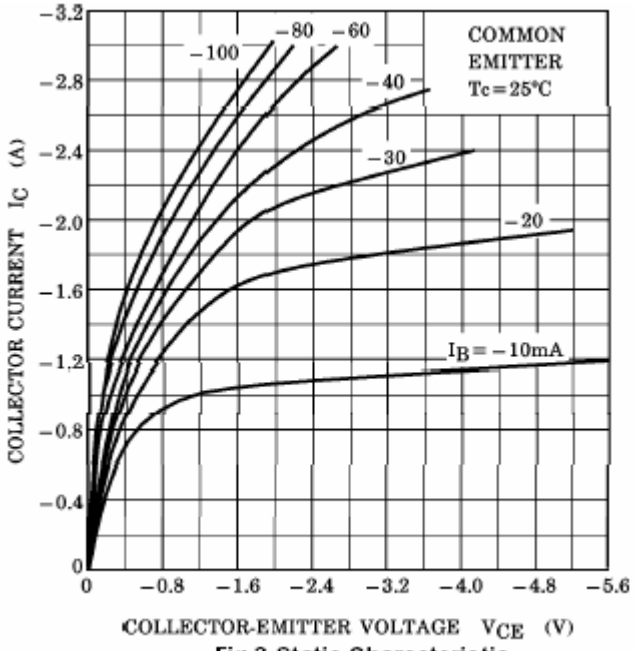

Fig.3 Static Characteristic

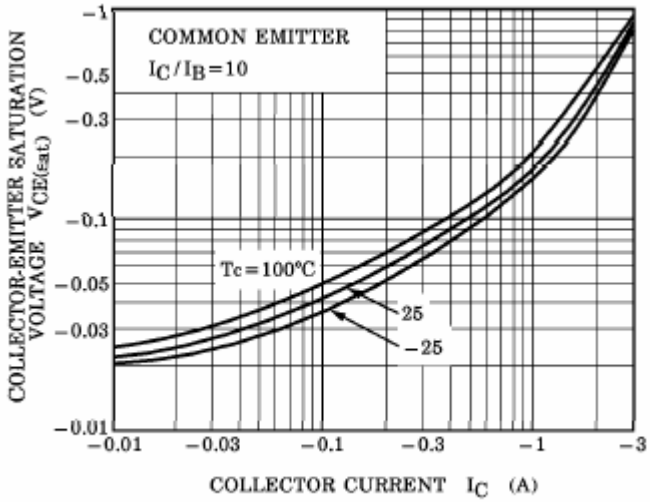

Fig.5 Collector-Emitter Saturation Voltage

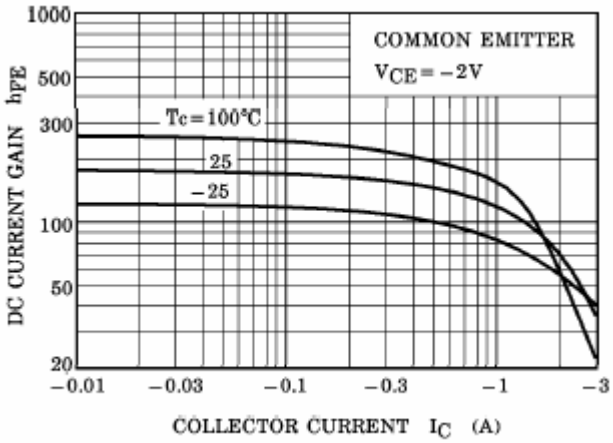

Fig.4 DC current Gain

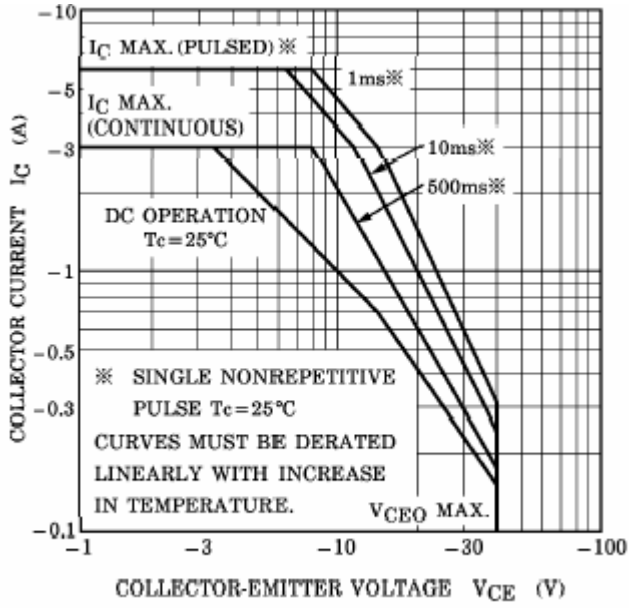

Fig.6 Safe Operating Area